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ESD3V3D3

Features

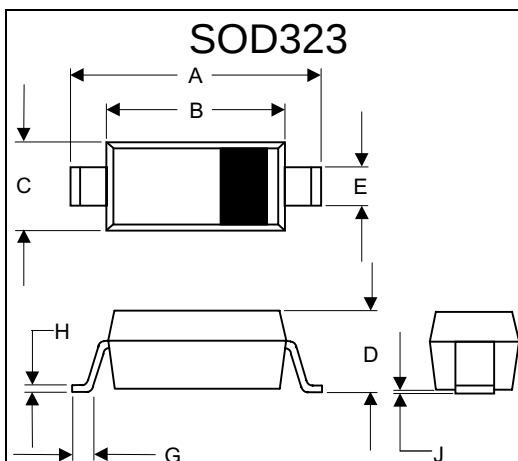
- For sensitive ESD protection
 - Low clamping voltage
 - Low leakage
 - Protects one power or I/O port
 - ESD protection > 40 kV
 - Fast response ,response time less than 1ns.
- Epoxy meets UL 94 V-0 flammability rating
Moisture Sensitivity Level 1

Maximum Ratings

- Operating Junction &StorageTemperature: -55°C to +150°C

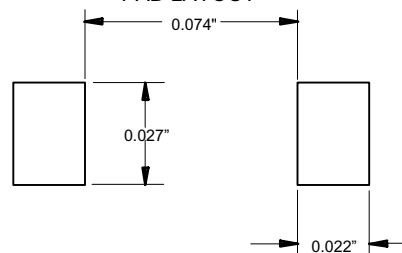
Parameter	Symbol	Limits	unit
IEC61000-4-2(ESD) Air Contact		± 15 ± 8	KV
ESD Voltage per human body mode		40	KV
Power Dissipation	Ppp	500	W

3.3Volts ESD Protection Devices



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.090	.107	2.30	2.70	
B	.063	.071	1.60	1.80	
C	.045	.053	1.15	1.35	
D	.031	.045	0.80	1.15	
E	.010	.016	0.25	0.40	
G	.004	.018	0.10	0.45	
H	.004	.010	0.10	0.25	
J	-----	.006	-----	0.15	

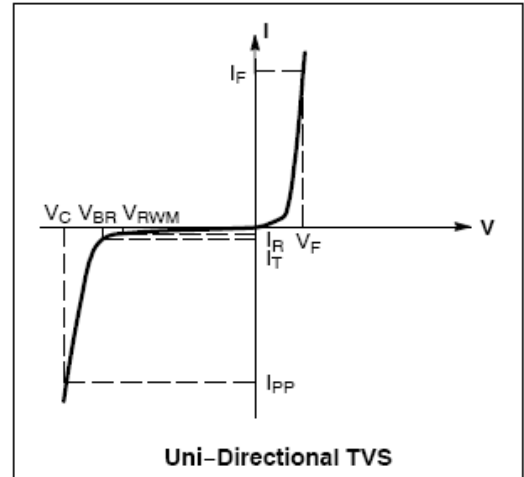
SUGGESTED SOLDER PAD LAYOUT





ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @ $V_R=0$ and $f=1\text{MHz}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Device	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)		I_T	V_C @ $I_{PP} = 7\text{ A}$	C_j (pF) $V_R=0\text{V}$
		Max	Max	Min	Max	mA	V	Typ
ESD3V3D3	---	3.3	1.0	5.0	---	1.0	9.3	100



TYPICAL CHARACTERISTICS

FIGURE 1
PEAK PULSE POWER VS PULSE TIME

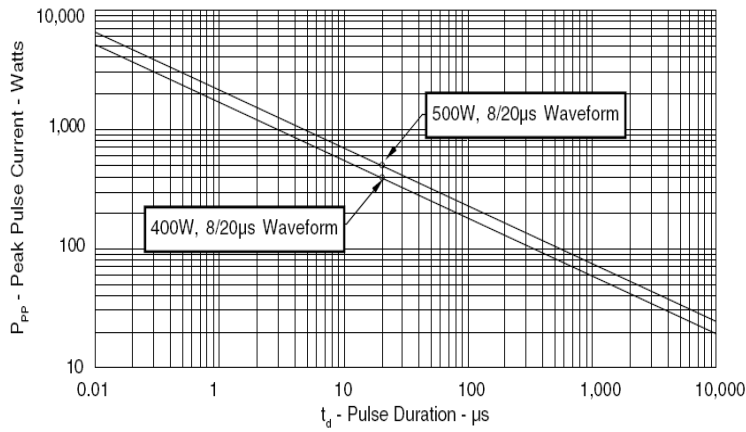


FIGURE 2
PULSE WAVE FORM

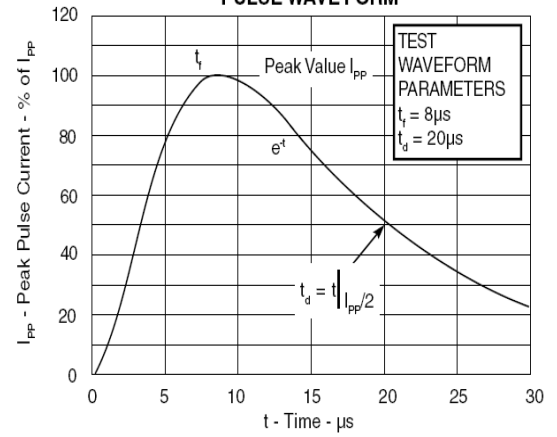


FIGURE 3
POWER DERATING CURVE

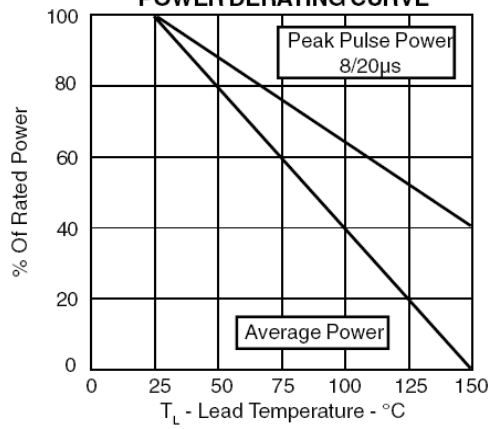


FIGURE 4
TYPICAL REVERSE VOLTAGE VS CAPACITANCE

